



Patent Application No. 10/657,505  
Customer Number: 42717

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Chii-Ming Wu

Serial No.: 10/657,505

Filing Date: September 8, 2003

For: METHOD OF MANUFACTURING A CONTACT  
INTERCONNECTION LAYER CONTAINING  
A METAL AND NITROGEN BY ATOMIC  
LAYER DEPOSITION FOR DEEP SUB-MICRON  
SEMICONDUCTOR TECHNOLOGY

§ Docket No.: 24061.406  
§ (TSMC2001-1247)  
§  
§ Examiner: Kennedy, Jennifer M.  
§  
§ Art Unit: 2812

**RESPONSE TO RESTRICTION REQUIREMENT**

Mail Stop: Amendment  
Commissioner for Patents  
PO Box 1450  
Alexandria, VA 22313-1450

Dear Sir:

In response to the second Office Action mailed June 30, 2005, Applicant thanks the Examiner for the additional time for reply and has identified the claims as required below:

Claims 1-25 as readable on Figs. 2a-2c and Fig. 3.  
Claims 1-3, 5-16, and 18-25 as readable on Group A-1 (Ti(OCH(CH<sub>3</sub>)<sub>2</sub>)<sub>4</sub>).  
Claims 1-25 as readable on Group C-1 (MN).  
Claims 1-24 as readable on Group D-1 (CMP).

Applicant withdraws the selection of Group B-1 (Silicon gas source) as this group contains limitations that do not exist in the selected embodiment.

An early action on the merits is respectfully requested.

Respectfully submitted,

*Timothy F. Bliss*

Timothy F. Bliss  
Reg. No. 50,925

Date: 7/19/05

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**CERTIFICATE OF MAILING**

I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to: Mail Stop: Amendment, Commissioner For Patents, PO Box 1450, Alexandria, VA 22313-1450 on the date below.

*Dayle Conner*  
Name  
7-22-05  
Date